

ABSTRACT OF THE DISCLOSURE

A semiconductor device comprising an insulation layer formed on a surface of a semiconductor substrate, a wiring groove pattern which is formed in the insulation layer, a conductive diffusion-prevention layer which is formed on the inner surface of the wiring groove, and a Cu-based wiring layer formed in the wiring groove provided on the inner surface thereof with the conductive diffusion-prevention layer, wherein the Cu-based wiring contains sulfur at a ratio ranging from 10^{-3} atomic % to 1 atomic %.

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